Electronic supplementary information

Efficient Planar Perovskite Solar Cells via Low-Pressure Vapor-Assisted Solution Process with TiO₂/Fullerene as Electron Collection

Bilayer

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Fig. S1 AFM images of (a) bare FTO substrate, (b) TiO_2 layer on FTO substrate, and C_{60} layers on TiO_2/FTO substrate (c) before and (d) after processed with DMF solution.



Fig. S2 Transmission spectra of $FTO/TiO_2/C_{60}$ -x (x=2, 6, 10, and 14) samples before and after processed with DMF solutions.



Fig. S3 Cross-sectional SEM images of $FTO/TiO_2/C_{60}$ -*x* samples. (a) *x*=0. Only TiO₂ layer was deposited on the FTO substrate. (b) and (c) *x*=2. (d) and (e) *x*=6. (f) and (g) *x*=10. (h) and (i) *x*=14. (b), (d), (f) and (h) are the as-fabricated samples without the

DMF process. (c), (e), (g) and (i) are samples after the DMF blank solvent coating process. Multipoint measurement method was used to obtained the thicknesses from the SEM images. The average thicknesses of the C_{60} -x (x=2, 6, 10 and 14) layers before and after the DMF processes were calculated by the differences between the thicknesses of the TiO₂/C₆₀-x (x=2, 6, 10 and 14) layers and the TiO₂/C₆₀-x (x=0) layer, which were summarized in (j).



Fig. S4 AFM images of PbI₂ layer prepared through spin coating on (a) FTO/TiO_2 and (b) $FTO/TiO_2/C_{60}$ -6 substrates.



Fig. S5 XRD patterns of (a) $FTO/TiO_2/C_{60}/PbI_2$ samples and (b) $FTO/TiO_2/C_{60}/CH_3NH_3PbI_3$ samples depend on the C_{60} solution concentration.



Fig. S6 SEM images of the C_{60} /FTO (a) before and (b) after processed with DMF



Fig. S7 J-V curves of PSCs with and without c-TiO₂ layer under light and dark

conditions



Fig. S8 (a) Current-voltage curves of PSCs without and with C_{60} interface layers which were prepared with different solution concentrations in dark. Data in (a) were

fitted with the formula: $V = R_s I + (\ln I - \ln I_s)AkT/q$ or $I\frac{dV}{dI} = R_s I + AkT/q$. (b)

Plots of $I^*(dV/dI)$ vs I which data came from curves in (a) and the linear fitting curves. (c) Series resistances (R_s) and ideal factors (A) derived from fitting curves in (b).



Fig. S9 *J*–*V* curves of the PSC with a high PCE via an all-solution process.